

SANYO Semiconductors DATA SHEET



N-Channel Silicon MOSFET 2SK4198FG — General-Purpose Switching Device **Applications**

Features

- · Low ON-resistance, low input capacitance, ultrahigh-speed switching.
- · Adoption of high reliability HVP process.
- · Attachment workability is good by Mica-less package.
- Avalanche resistance guarantee.

Specifications

Absolute Maximum Ratings at Ta=25°C

| Parameter | Symbol | Conditions | Ratings | Unit |
|------------------------------------|--------------------|--|-------------|------|
| Drain-to-Source Voltage | VDSS | | 600 | V |
| Gate-to-Source Voltage | VGSS | | ±30 | V |
| Drain Current (DC) | I _{Dc} *1 | Limited only by maximum temperature Tch=150°C | 5 | А |
| | IDpack *2 | Tc=25°C (SANYO's ideal heat dissipation condition)*3 | 4 | Α |
| Drain Current (Pulse) | IDP | PW≤10μs, duty cycle≤1% | 18 | Α |
| Allowable Power Dissipation | D- | | 2.0 | W |
| | PD | Tc=25°C (SANYO's ideal heat dissipation condition)*3 | 30 | W |
| Channel Temperature | Tch | | 150 | °C |
| Storage Temperature | Tstg | | -55 to +150 | °C |
| Avalanche Energy (Single Pulse) *4 | EAS | | 55 | mJ |
| Avalanche Current *5 | IAV | | 4.5 | Α |

Note :*1 Shows chip capability.

*2 Package limited.

*3 SANYO's condition is radiation from backside.

The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

*4 VDD=50V, L=5mH, IAV=4.5A

*5 L≤5mH, Single pulse

Marking: K4198

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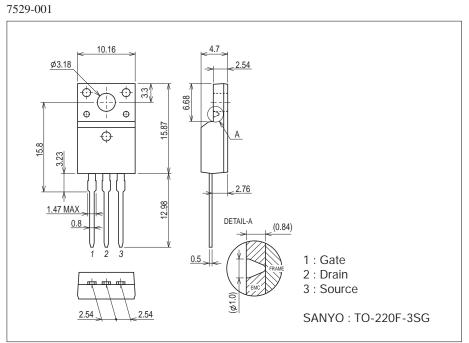
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Electrical Characteristics at Ta=25°C

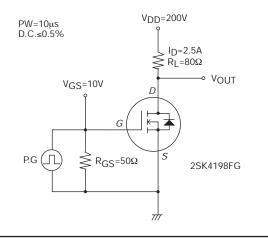
| Parameter | Symbol | Conditions | Ratings | | | 1.114 |
|--|-----------------------|---|---------|------|------|-------|
| | | | min | typ | max | Unit |
| Drain-to-Source Breakdown Voltage | V(BR)DSS | ID=10mA, VGS=0V | 600 | | | V |
| Zero-Gate Voltage Drain Current | IDSS | V _{DS} =480V, V _{GS} =0V | | | 100 | μΑ |
| Gate-to-Source Leakage Current | IGSS | V _{GS} =±30V, V _{DS} =0V | | | ±100 | nA |
| Cutoff Voltage | V _{GS} (off) | V _{DS} =10V, I _D =1mA | 3 | | 5 | V |
| Forward Transfer Admittance | yfs | V _{DS} =10V, I _D =2.5A | 1.2 | 2.4 | | S |
| Static Drain-to-Source On-State Resistance | R _{DS} (on) | ID=2.5A, VGS=10V | | 1.8 | 2.34 | Ω |
| Input Capacitance | Ciss | V _{DS} =30V, f=1MHz | | 360 | | pF |
| Output Capacitance | Coss | V _{DS} =30V, f=1MHz | | 69 | | pF |
| Reverse Transfer Capacitance | Crss | VDS=30V, f=1MHz | | 15 | | pF |
| Turn-ON Delay Time | t _d (on) | See specified Test Circuit. | | 13 | | ns |
| Rise Time | tr | See specified Test Circuit. | | 28 | | ns |
| Turn-OFF Delay Time | t _d (off) | See specified Test Circuit. | | 39 | | ns |
| Fall Time | tf | See specified Test Circuit. | | 15 | | ns |
| Total Gate Charge | Qg | VDS=200V, VGS=10V, ID=5A | | 14.3 | | nC |
| Gate-to-Source Charge | Qgs | V _{DS} =200V, V _{GS} =10V, I _D =5A | | 3.0 | | nC |
| Gate-to-Drain "Miller" Charge | Qgd | V _{DS} =200V, V _{GS} =10V, I _D =5A | | 8.2 | | nC |
| Diode Forward Voltage | V _{SD} | IS=5A, VGS=0V | | 0.9 | 1.2 | V |

Package Dimensions

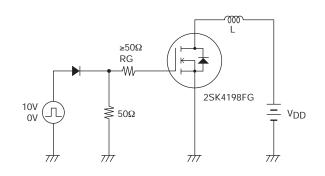
unit : mm (typ)



Switching Time Test Circuit



Avalanche Resistance Test Circuit



2SK4198FG

For this package, a part of inner electrode is exposed. Please refer to the package outline for the detailedstructure.

So when mounting the device, please pay enough attention to the isolation with the heatsink.

According to the device mounting method, sometimes the insulation voltage may be decreased. (refer to the below insulation characteristics)

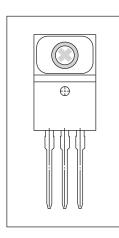
Insulation / Ta=25°C / RH75%

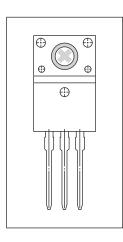
| Parameter | Symbol | Conditions | Ratings | | | Unit |
|---------------------------|--------|-----------------------------------|---------|------|-----|-------|
| | | | min | typ | max | UTIIL |
| Lead & resin insulation * | VISO1 | Metal spacer Refer to Fig.1 | | 1600 | | Vrms |
| | VISO2 | Washer 5.8mm Refer to Fig.2 | | 2100 | | Vrms |
| | VISO3 | Insulated screw, Insulated washer | | 3900 | | Vrms |

*: AC voltage measurement

Fig.1

Fig.2

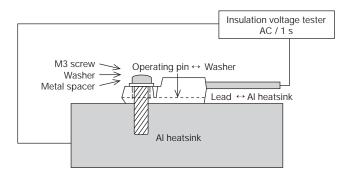




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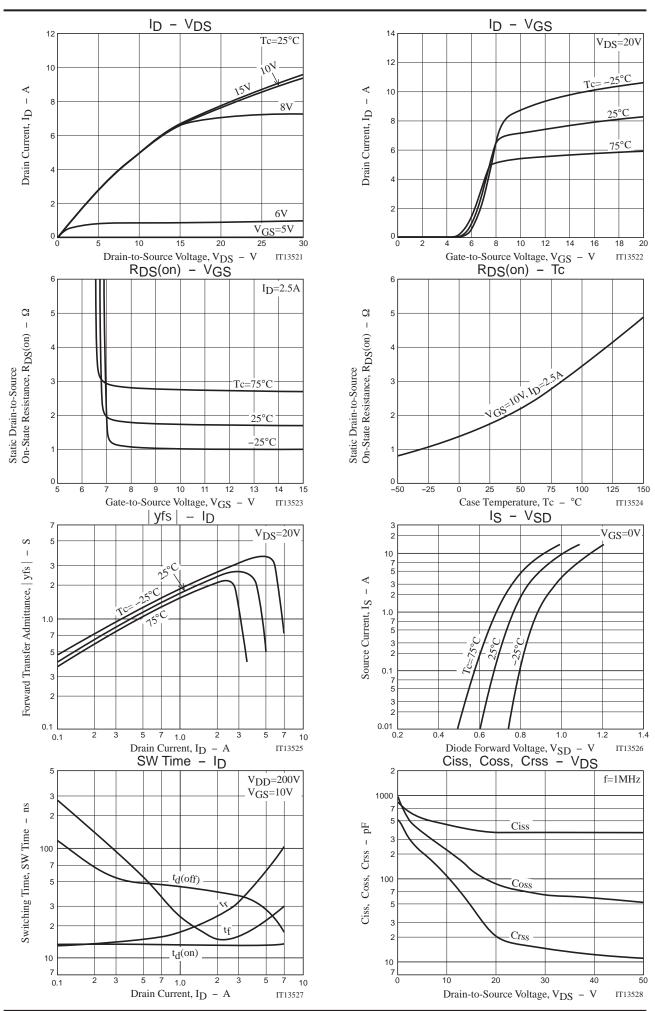
IT14078

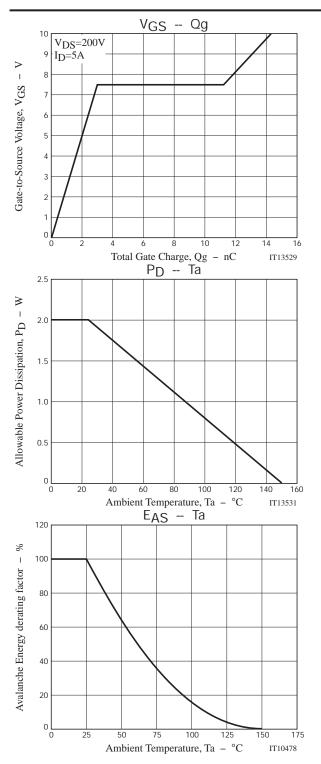
Insulation Measuring Diagram

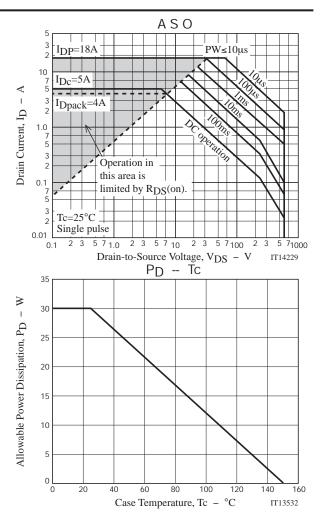


IT14079

2SK4198FG







Note on usage : Since the 2SK4198FG is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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